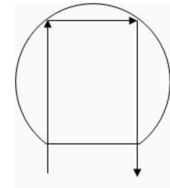
Part Number	Customer

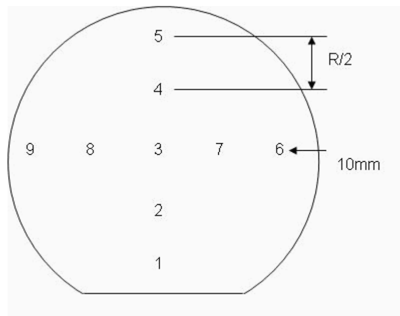
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Length	None	Wafer Vendor
	5.0	Overall Thickness	452.40 +/- 7.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	
	7.0	Bow	<100.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<100.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	350.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1~20 Ohmcm	Wafer Vendor
	17.0	Handle Oxygen Concentration	<15 ppma (ASTM F121-83)	Wafer vendor
	18.0	Backside Finish	Polished with light handling marks, oxide and laser marking	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	24,000.00 +/- 1,200.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle Wafer Only	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	24.0	Nominal Thickness	100.00 +/- 1.00 µm	Fimetrics 9 point, 100%.
	25.0	Distance to device silicon edge from wafer edge	<= 2mm EDGE DEFINED	Typical by process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	0.01 ~ 0.02 Ohmcm	Wafer Vendor
	29.0	Oxygen Concentration	<15 ppma (ASTM F121-83)	Wafer vendor
	30.0	Voids	none	Bright Light, 100% (note 2)
	31.0	Scratches	Max total length 10mm	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)
	33.0	Device Field Oxidation	2,000.00 +/- 200.00 A	Nanospec centre point, 4%

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information